

**WHAT IS CLAIMED IS:**

1. A tiedown structure, comprising:
  - a semiconductor substrate having a chip formed thereon;
  - a kerf region proximate the chip; and
  - a conductive connector forming a connection between the chip and the kerf region.
2. The tiedown structure of claim 1, further comprising:
  - an edge seal along an outer perimeter of the chip,
  - wherein the conductive connector crosses the edge seal.
3. The tiedown structure of claim 2, wherein the conductive connector is not in electrical communication with the edge seal.
4. The tiedown structure of claim 1, wherein the conductive connector is a metal line.
5. The tiedown structure of claim 1, wherein the chip comprises a device and the conductive connector is in electrical communication with the device and the kerf region.
6. The tiedown structure of claim 5, wherein the conductive connector is in electrical communication with ground potential in the kerf region.
7. A tiedown structure comprising:
  - a semiconductor substrate having a chip formed thereon;
  - an edge seal along an outer perimeter of the chip; and
  - a conductive connector forming a connection between the edge seal and a portion of the chip.
8. The tiedown structure of claim 5, wherein the chip comprises a device and the conductive connector is in electrical communication with the device and the edge seal.
9. The tiedown structure of claim 7, wherein the conductive connector is a metal line.

10. A method for forming a semiconductor structure, comprising:
  - forming a device on a chip;
  - defining a kerf proximate the chip; and
  - forming a conductive connector, the conductive connector connecting the device and the kerf.
11. The method of claim 10, wherein forming a conductive connector comprises forming a metal line.
12. The method of claim 10, wherein the conductive connector connecting the device and the kerf connects the device to ground potential in the kerf.
13. The method of claim 10, further comprising:
  - removing an end of the conductive connector from the kerf.
14. The method of claim 13, wherein removing an end of the conductive connector comprises sawing through the kerf.
15. The method of claim 13, wherein removing an end of the conductive connector comprises etching.
16. The method of claim 13, wherein removing an end of the conductive connector comprises focused ion beam milling.
17. A method for forming a semiconductor structure, comprising:
  - forming a chip on a semiconductor substrate, the chip including a device;
  - forming an edge seal along an outer perimeter of the chip; and
  - forming a conductive connector, the conductive connector connecting the edge seal and the device.

18. The method of claim 17, wherein forming a conductive connector comprises forming a metal line.
19. The method of claim 17, wherein the conductive connector connecting the edge seal and the device connects the device to ground potential in the edge seal.
20. The method of claim 17, further comprising:  
removing a portion of the conductive connector.
21. The method of claim 20, wherein removing the portion of the conductive connector comprises removing a portion of the conductive connector between the edge seal and the device.
22. The method of claim 21, wherein removing the portion of the conductive connector comprises etching.
23. The method of claim 21, wherein removing the portion of the conductive connector comprises focused ion beam milling.